IN THE SPECIFICATION

At page 3, line 19, please add the following:

REFERENCES

Y. Yamaguchi et al., "Properties of Heteroepitaxial 3C-SiC Films Grown by LPCVD", 8th International Conference on Solid-State Sensors and Actuators and Eurosensors IX, Digest of Technical Papers, page 3. vol. (934+1030+85), pages 190-3, Vol. 2, 1995;

M. Andrieux, et al., "Interface and Adhesion of PECVD SiC Based Films on Metals", Le Vide Science, Technique et Applications. (France), No. 279, pages 212-214, 1996;

F. Lanois, "Angle Etch Control for Silicon Power Devices", Applied Physics Letters, Vol 69, No. 2, pages 236-238, July 1996;

N. J. Dartnell, et al., "Reactive Ion Etching of Silicon Carbide" Vacuum, Vol. 46, No. 4, pages 349-355, 1955.

The paragraph beginning at page 22, line 18 is amended as follows:

In one embodiment, for example, SiC film **1206** is deposited using low-pressure chemical vapor deposition (LPCVD), providing the structure illustrated in Figure **12C**. The LPCVD process uses either a hot-wall reactor or a cold-wall reactor with a reactive gas, such as a mixture of $Si(CH_3)_4$ and Ar. ~~Examples of such processes are disclosed in an article by Y. Yamaguchi et al., entitled "Properties of Heteroepitaxial 3C-SiC Films Grown by LPCVD", in the 8th International Conference on Solid-State Sensors and Actuators and Eurosensors IX, Digest of Technical Papers, page 3. vol. (934+1030+85), pages 190-3, Vol. 2, 1995, and in an article by M. Andrieux, et al., entitled "Interface and Adhesion of PECVD SiC Based Films on Metals", in supplement Le Vide Science, Technique et Applications. (France), No. 279, pages 212-214, 1996.~~ However, SiC film **1206** can be deposited using other techniques such as, for example, enhanced CVD techniques known to those skilled in the art including low pressure rapid thermal chemical vapor deposition (LP-RTCVD), or by decomposition of hexamethyl disalene using ArF excimer laser irradiation, or by low temperature molecular beam epitaxy (MBE). Other examples of forming SiC film **1206** include reactive magnetron sputtering, DC plasma discharge,

ion-beam assisted deposition, ion-beam synthesis of amorphous SiC films, laser crystallization of amorphous SiC, laser reactive ablation deposition, and epitaxial growth by vacuum anneal. The conductivity of the SiC film **1206** can be changed by ion implantation during subsequent process steps, such as during the self-aligned formation of source/drain regions for the n-channel and p-channel FETs.

The paragraph beginning at page 23, line 10 is amended as follows:

In Figure **12D**, SiC film **1206** is patterned and etched, together with thin oxide layer **118**, to form SiC gate **106**. SiC film **1206** is patterned using standard techniques and is etched using plasma etching, reactive ion etching (RIE) or a combination of these or other suitable methods. For example, SiC film **1206** can be etched by RIE in a distributed cyclotron resonance reactor using a SF_6 /O_2 gas mixture using SiO_2 as a mask with a selectivity of 6.5. ~~Such process is known in the art and is disclosed, for example, in an article by F. Lanois, entitled "Angle Etch Control for Silicon Power Devices", which appeared in Applied Physics Letters, Vol 69, No. 2, pages 236-238, July 1996.~~ Alternatively, SiC film **1206** can be etched by RIE using the mixture SF_6 and O_2 and $F_2/Ar/O_2$. ~~An example of such a process is disclosed in an article by N. J. Dartnell, et al., entitled "Reactive Ion Etching of Silicon Carbide" in Vacuum, Vol. 46, No. 4, pages 349-355, 1955.~~ The etch rate of SiC film **1206** can be significantly increased by using magnetron enhanced RIE.